

Silicon nanotapers for fiber-to-waveguide coupling

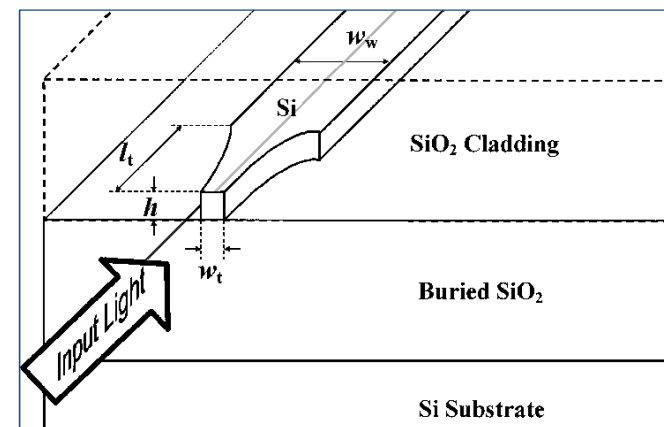
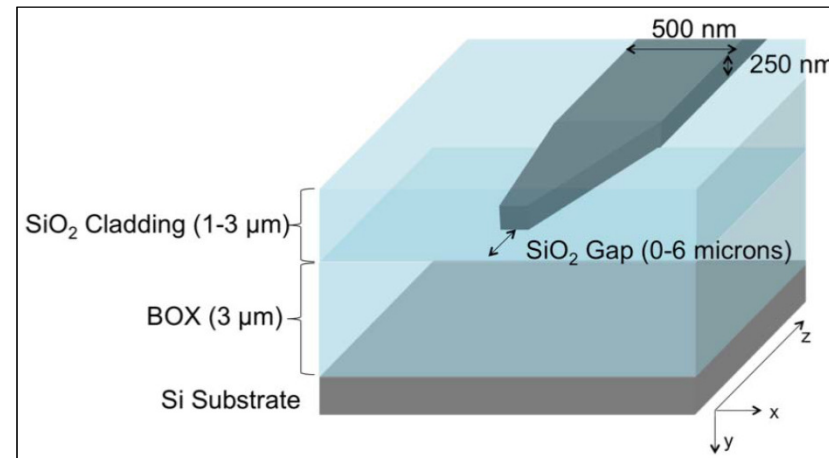


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Introduction

- The two main approaches for coupling light on a high-confinement chip with sub-micron waveguides are gratings, or taper couplers. [1]
- The coupler is composed of high-index-contrast materials and is based on a short taper with a nanometer-sized tip. [2]
- The tapered coupler is actually a compact mode convertor between a fiber and a sub-micrometer waveguide. [2]
- The tapered coupler can be linear [1] or parabolic [2] transition.
- Silicon-on-insulator (SOI) technology was chosen as the platform for the nanotaper and waveguides because it provides a high-index contrast, includes a SiO_2 layer as an optical buffer, and permits compatibility with integrated electronic circuits. [2]



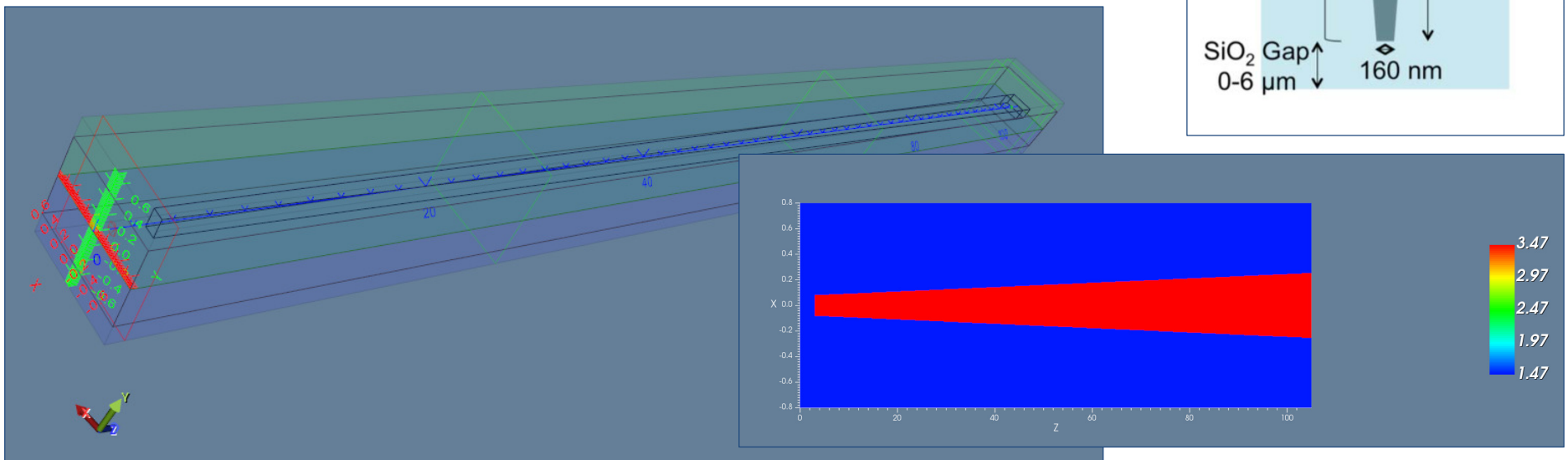
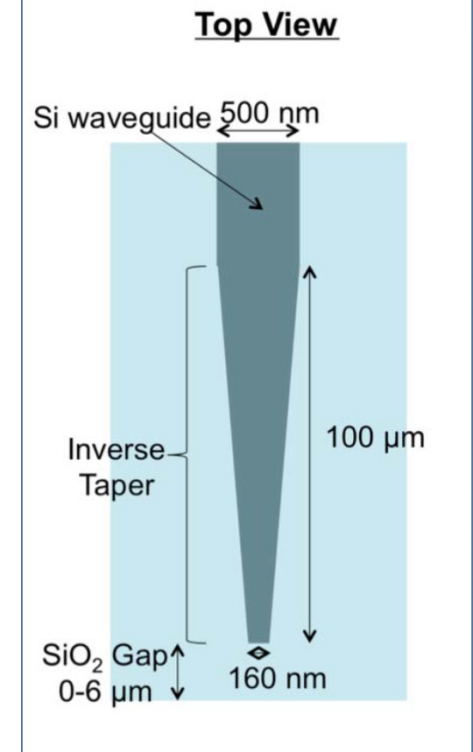
[1] Jaime Cardenas, et al., "High Coupling Efficiency Etched Facet Tapers in Silicon Waveguides," *IEEE Phot. Tech. Lett.* VOL. 26, NO. 23, 2380-2382 (2014)

[2] Vilson R. Almeida, et al., "Nanotaper for compact mode conversion," *Opt. Lett.* **28**, 1302-1304 (2003);

3D FDTD simulation

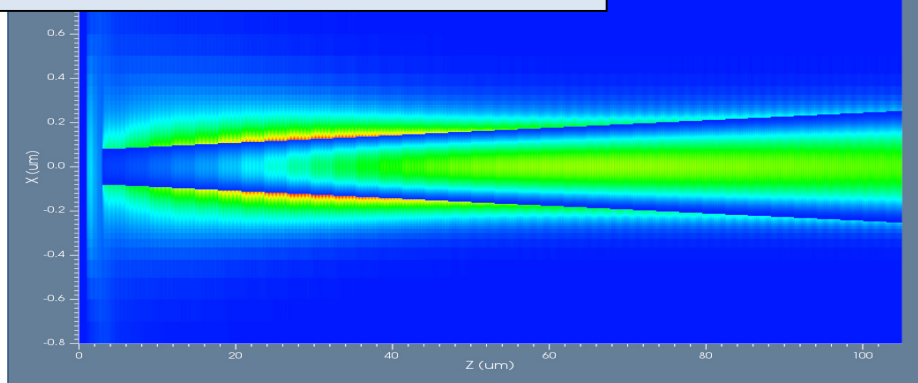
- The key component to be simulated is the linearly tapered Si waveguide (160 nm to 500 nm width change over 100 μm length, 250 nm height) from Ref. [1], which is buried in SiO_2 waveguide (Note: A reduced size was used (1.5 $\mu\text{m} \times 1.5 \mu\text{m} \times 105 \mu\text{m}$) to allow for a faster simulation time)
- For the accurate simulation of a linearly tapered Si waveguide, the mesh size for the taper should be fine, therefore non-uniform mesh is used in this case.
- The optical source is set as CW ($\lambda=1.55 \mu\text{m}$) in the time domain with a Gaussian transverse profile in the spatial domain and is located at the Si paper tip of the SiO_2 waveguide.

Note: The simulation time should be made long enough to ensure a steady state result

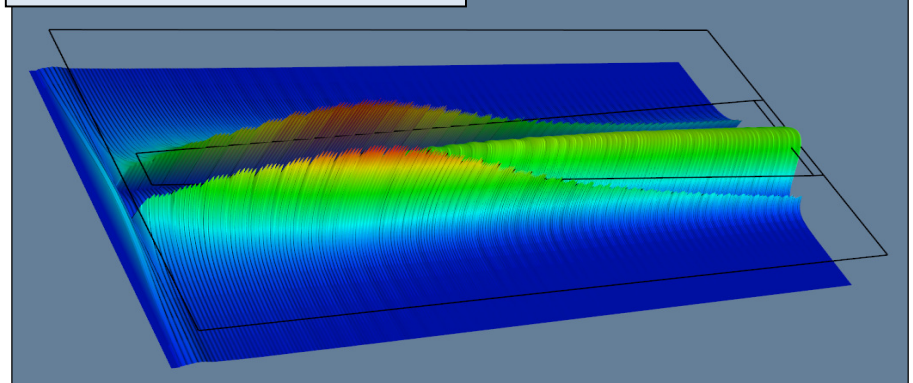


Simulation results

Image map of E_x intensity profile (top view)

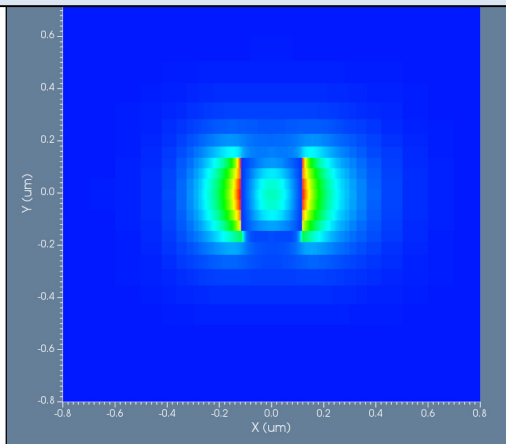


Height plot of E_x intensity profile

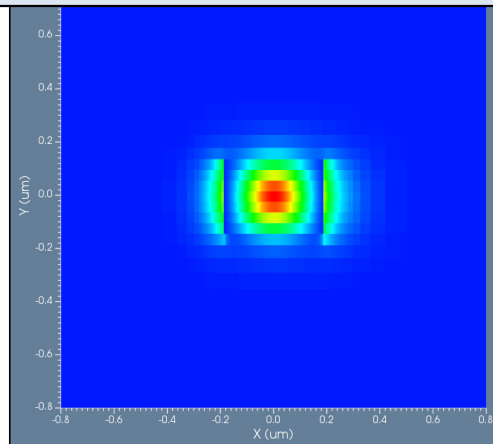


- The top view demonstrates the efficient coupling of the tapered Si waveguide.
- The bottom view shows the mode conversion at different positions (left: 25 μm , middle: 65 μm , right: 103 μm)

E_x intensity profile (cross section – 25 μm)



E_x intensity profile (cross section – 65 μm)



E_x intensity profile (cross section – 103 μm)

